XPT IGBT

IXA2201650NA

tentative

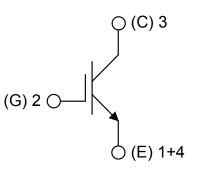
V_{CES}	=	650 V
_{C25}	=	255A
$V_{\text{CE(sat)}}$	=	1.6V

Single IGBT

Part number IXA2201650NA



Backside: isolated **E**72873



Features / Advantages:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through)
- results in: - short circuit rated for 10 µsec.
- very low gate charge
- low EMI
- square RBSOA @ 2x lc
- Thin wafer technology combined with the XPT design results in a competitive low VCE(sat)

Applications:

- AC motor drives
- Solar inverter
- Medical equipment

• Pumps, Fans

- Uninterruptible power supply
- Air-conditioning systems

• Inductive heating, cookers

- Welding equipment
 Switched-mode and resonant-mode power supplies
- Advanced power cycling • Either emitter terminal can be used as main or Kelvin emitter

Package: SOT-227B (minibloc)

 Isolation Voltage: 3000 V~ Industry standard outlineRoHS compliant

• Epoxy meets UL 94V-0 Base plate: Copper internally DCB isolated

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IGBT						Ratings	5	
Symbol	Definition		Conditions		min.	typ.	max.	Unit
V _{CES}	collector emitter voltage			$T_{VJ} = 25^{\circ}C$			650	V
V _{GES}	max. DC gate voltage						±20	V
V_{GEM}	max. transient gate emitter voltage						±30	V
I _{C25}	collector current			$T_c = 25^{\circ}C$			255	A
I _{C 80}				$T_c = 80^{\circ}C$			156	A
P _{tot}	total power dissipation			$T_c = 25^{\circ}C$			625	W
V _{CE(sat)}	collector emitter saturation voltage		I _c = 200A; V _{GE} = 15 V	$T_{vJ} = 25^{\circ}C$		1.6	1.8	V
				T _{vJ} = 125°C		1.9		V
V _{GE(th)}	gate emitter threshold voltage		I_{c} = 3.2mA; V_{GE} = V_{CE}	$T_{vJ} = 25^{\circ}C$	4	4.8	5.5	V
ICES	collector emitter leakage current		$V_{CE} = V_{CES}; V_{GE} = 0 V$	$T_{vJ} = 25^{\circ}C$			0.1	mA
				T _{vJ} = 125°C		0.1		mA
I _{GES}	gate emitter leakage current		$V_{GE} = \pm 20 V$				500	nA
Q _{G(on)}	total gate charge		V_{CE} = 300 V; V_{GE} = 15 V; I_{C} =	200 A		280		nC
t _{d(on)}	turn-on delay time	٦				30		ns
t,	current rise time			T (05%)		50		ns
t _{d(off)}	turn-off delay time		inductive load	T _{vJ} = 125°C		100		ns
t _f	current fall time	7	$V_{CE} = 300 \text{ V}; I_C = 200 \text{ A}$			40		ns
Eon	turn-on energy per pulse		V_{GE} = ±15 V; R_G = 3.9 Ω			2		mJ
E _{off}	turn-off energy per pulse	J				7.6		mJ
RBSOA	reverse bias safe operating area	٦	V_{GE} = ±15 V; R_{G} = 3.9 Ω	T _{vJ} = 125°C				
I _{CM}		ſ	$V_{CEmax} = 650 V$				400	A
SCSOA	short circuit safe operating area	٦	V _{CEmax} = 650 V					
tsc	short circuit duration	}	V_{CE} = 360 V; V_{GE} = ±15 V	T _{vJ} = 125°C			10	μs
l _{sc}	short circuit current	J	R_{g} = 3.9 Ω ; non-repetitive			800		А
R _{thJC}	thermal resistance junction to case						0.2	K/W
R _{thCH}	thermal resistance case to heatsink					0.10		K/W

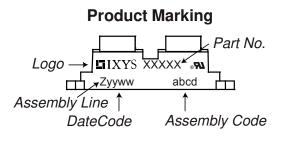


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Package	Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal 1)					150	Α
T _{vj}	virtual junction temperature)			-40		150	°C
T _{op}	operation temperature				-40		125	°C
T _{stg}	storage temperature				-40		150	°C
Weight						30		g
M _D	mounting torque				1.1		1.5	Nm
Μ _τ	terminal torque				1.1		1.5	Nm
d _{Spp/App}	oroopaga distance on surfa	ce striking distance through air	terminal to terminal	10.5	3.2			mm
d _{Spb/Apb}	creepage distance on suna		terminal to backside	8.6	6.8			mm
	isolation voltage	t = 1 second			3000			V
		t = 1 minute	50/60 Hz, RMS; Iıso∟ ≤ 1 mA		2500			V

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.



Part description

I = IGBT X = XPT IGBT A = Gen 1 / std 220 = Current Rating [A] I = Single IGBT

650 = Reverse Voltage [V] NA = SOT-227B (minibloc)

[Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
	Standard	IXA2201650NA	IXA2201650NA	Tube	10	514555

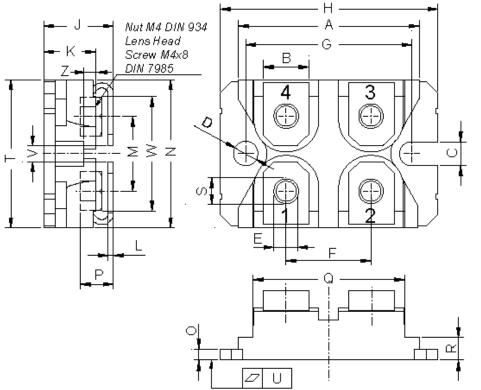
Equiv	alent Circuits for Simulation	* on die level	T _{vJ} = 150 °C
$I \rightarrow V_0$)-[IGBT	
V _{0 max}	threshold voltage	1.1	V
$R_{0 max}$	slope resistance *	5.3	mΩ



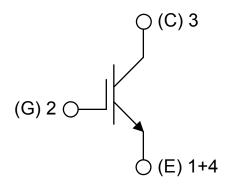
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Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches		
Dim.	min	max	min	max	
A	31.50	31.88	1.240	1.255	
в	7.80	8.20	0.307	0.323	
С	4.09	4.29	0.161	0.169	
D	4.09	4.29	0.161	0.169	
Е	4.09	4.29	0.161	0.169	
F	14.91	15.11	0.587	0.595	
G	30.12	30.30	1.186	1.193	
Н	37.80	38.23	1.488	1.505	
J	11.68	12.22	0.460	0.481	
К	8.92	9.60	0.351	0.378	
L	0.74	0.84	0.029	0.033	
Μ	12.50	13.10	0.492	0.516	
Ν	25.15	25.42	0.990	1.001	
0	1.95	2.13	0.077	0.084	
Ρ	4.95	6.20	0.195	0.244	
Q	26.54	26.90	1.045	1.059	
R	3.94	4.42	0.155	0.167	
S	4.55	4.85	0.179	0.191	
Т	24.59	25.25	0.968	0.994	
U	-0.05	0.10	-0.002	0.004	
V	3.20	5.50	0.126	0.217	
W	19.81	21.08	0.780	0.830	
Ζ	2.50	2.70	0.098	0.106	



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